

QORVO

SiC JFET Division

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DATASHEET

UJ3D1210KSD

Silicon Carbide (SiC) Diode - EliteSiC, TO-247-3L, 10 A, 1200 V SiC Merged PiN-Schottky (MPS) Dual Diode

Rev. D, Jan 2025

Description

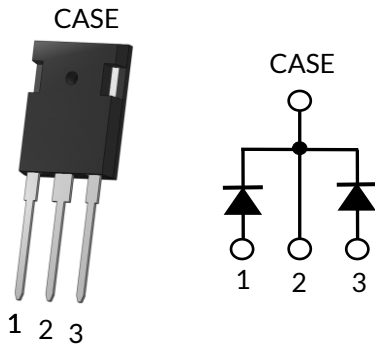
UnitedSiC offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.

Features

- ◆ Maximum operating temperature of 175°C
- ◆ Easy paralleling
- ◆ Extremely fast switching not dependent on temperature
- ◆ No reverse or forward recovery
- ◆ Enhanced surge current capability, MPS structure
- ◆ Excellent thermal performance, Ag sintered
- ◆ 100% UIS tested
- ◆ AEC-Q101 qualified
- ◆ AECQ Qualified

Typical applications

- ◆ Power converters
- ◆ Industrial motor drives
- ◆ Switch mode power supplies
- ◆ Power factor correction modules



Part Number	Package	Marking
UJ3D1210KSD	TO-247-3L	UJ3D1210KSD



Maximum Ratings

Parameter	Symbol	Test Conditions	Value (Leg/Device)	Units
DC blocking voltage	V_R		1200	V
Repetitive peak reverse voltage, $T_J=25^{\circ}\text{C}$	V_{RRM}		1200	V
Surge peak reverse voltage	V_{RSM}		1200	V
Maximum DC forward current	I_F	$T_C = 160.7^{\circ}\text{C}$	5/10	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	$T_C = 25^{\circ}\text{C}, t_p = 10\text{ms}$	70/140	A
		$T_C = 110^{\circ}\text{C}, t_p = 10\text{ms}$	63/126	
Repetitive forward surge current sine halfwave, $D=0.1$	I_{FRM}	$T_C = 25^{\circ}\text{C}, t_p = 10\text{ms}$	31.8/63.6	A
		$T_C = 110^{\circ}\text{C}, t_p = 10\text{ms}$	18.6/37.2	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^{\circ}\text{C}, t_p = 10\mu\text{s}$	525/1050	A
		$T_C = 110^{\circ}\text{C}, t_p = 10\mu\text{s}$	525/1050	
i^2t value	$\int i^2 dt$	$T_C = 25^{\circ}\text{C}, t_p = 10\text{ms}$	24.5/98	A^2s
		$T_C = 110^{\circ}\text{C}, t_p = 10\text{ms}$	19.5/78	
Power dissipation	P_{tot}	$T_C = 25^{\circ}\text{C}$	136/272	W
		$T_C = 160.7^{\circ}\text{C}$	13/26	
Maximum junction temperature	$T_{J,max}$		175	$^{\circ}\text{C}$
Operating and storage temperature	T_J, T_{STG}		-55 to 175	$^{\circ}\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Test Conditions	Value (Leg/Device)			Units
			Min	Typ	Max	
Thermal resistance, junction-to-case	$R_{\theta JC}$			0.85/0.425	1.1/0.55	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Value (Leg/Device)			Units
			Min	Typ	Max	
Forward voltage	V_F	$I_F = 5\text{A}/10\text{A}, T_J = 25^\circ\text{C}$	-	1.4	1.6	V
		$I_F = 5\text{A}/10\text{A}, T_J = 150^\circ\text{C}$	-	1.85	2.3	
		$I_F = 5\text{A}/10\text{A}, T_J = 175^\circ\text{C}$	-	2	2.6	
Reverse current	I_R	$V_R = 1200\text{V}, T_J = 25^\circ\text{C}$	-	5/10	55/110	μA
		$V_R = 1200\text{V}, T_J = 175^\circ\text{C}$	-	160/320		
Total capacitive charge ⁽¹⁾	Q_C	$V_R = 800\text{V}$		27/54		nC
Total capacitance	C	$V_R = 1\text{V}, f = 1\text{MHz}$		250/500		pF
		$V_R = 400\text{V}, f = 1\text{MHz}$		24.5/49		
		$V_R = 800\text{V}, f = 1\text{MHz}$		22/44		
Capacitance stored energy	E_C	$V_R = 800\text{V}$		8/16		μJ

(1) Q_C is independent on $T_J, di_f/dt$, and I_F as shown in the application note USCi_AN0011.

Typical Performance Diagrams (Per Leg)

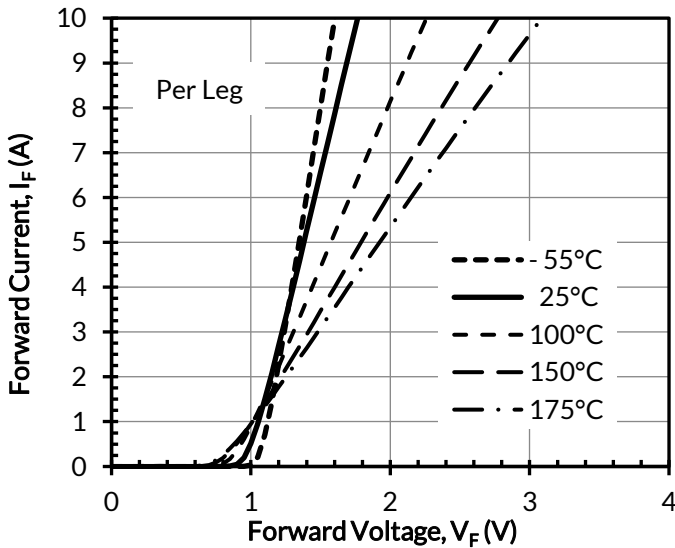


Figure 1. Typical forward characteristics

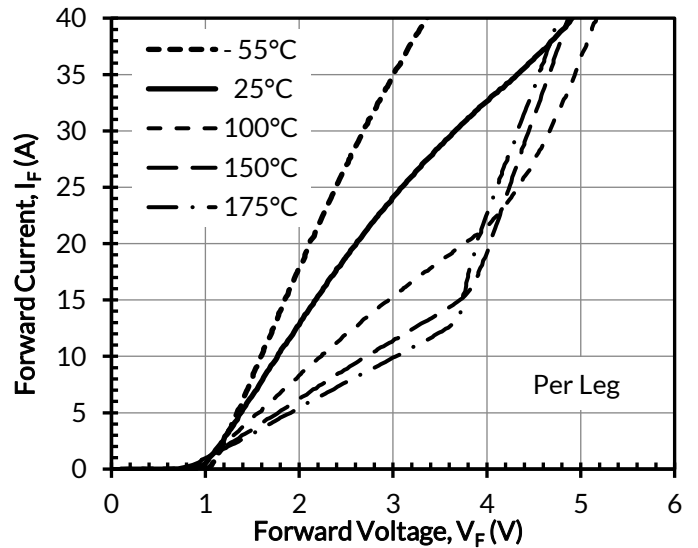


Figure 2. Typical forward characteristics in surge current

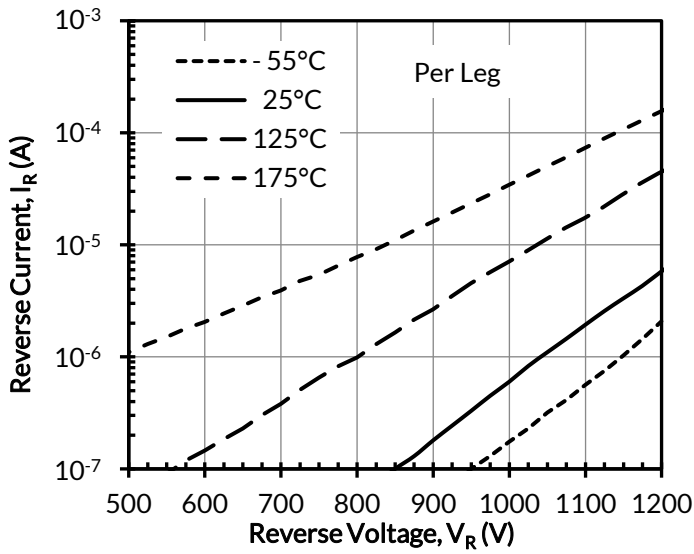


Figure 3. Typical reverse characteristics

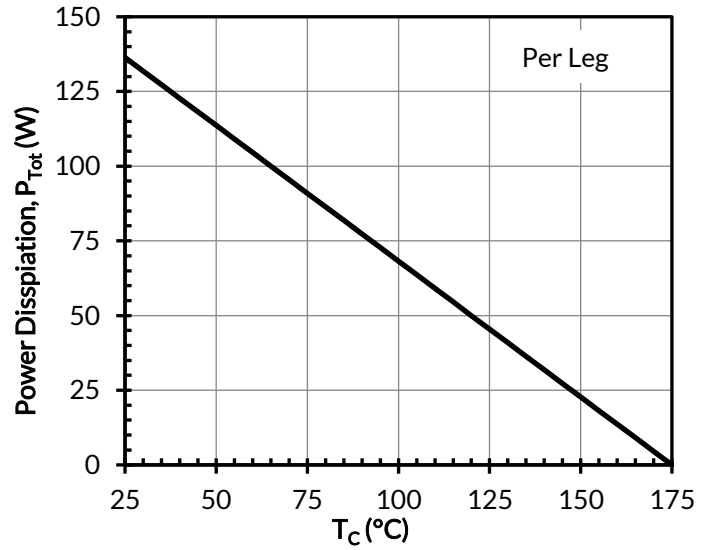


Figure 4. Power dissipation

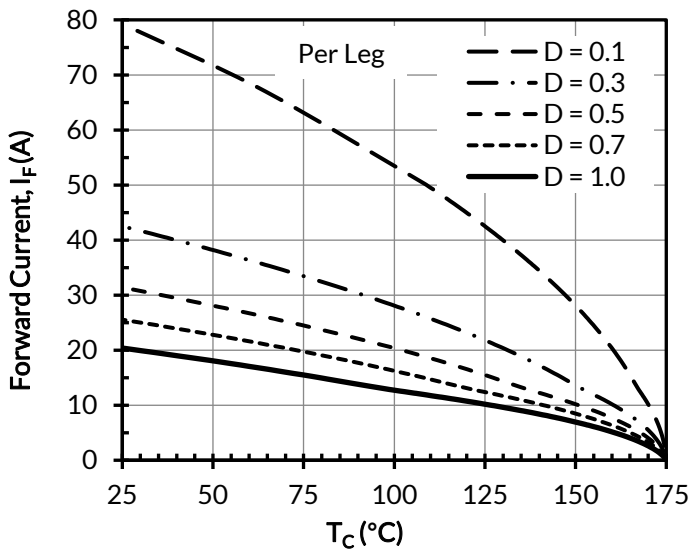


Figure 5. Diode forward current

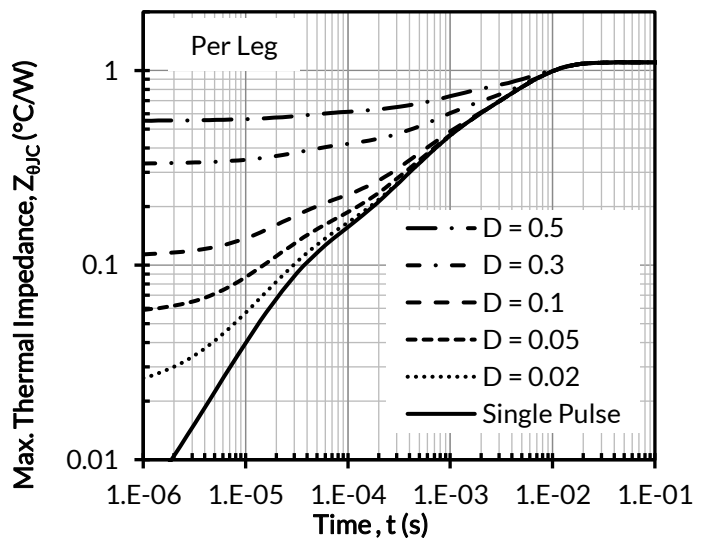


Figure 6. Maximum transient thermal impedance

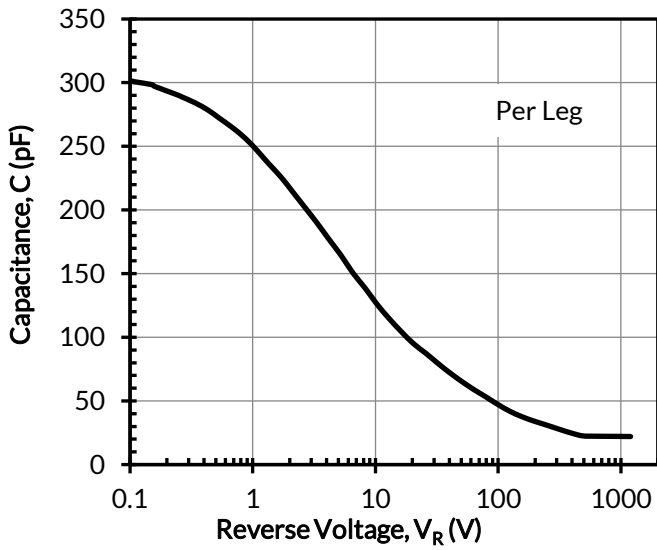


Figure 7. Capacitance vs. reverse voltage at 1MHz

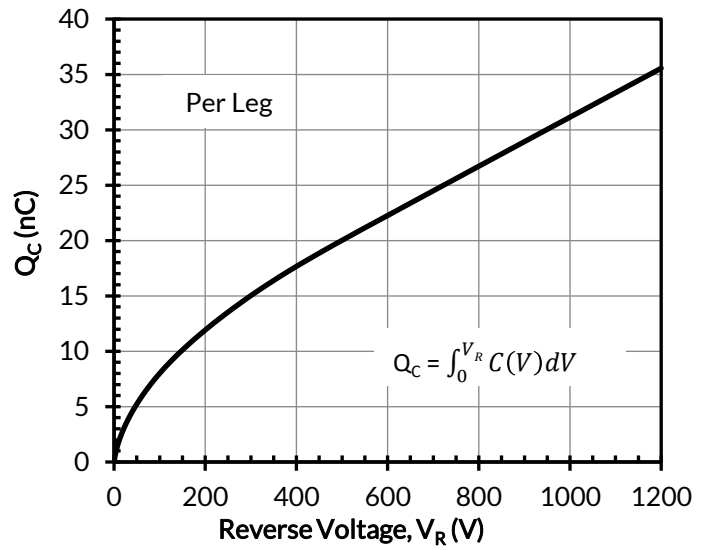


Figure 8. Typical capacitive charge vs. reverse voltage

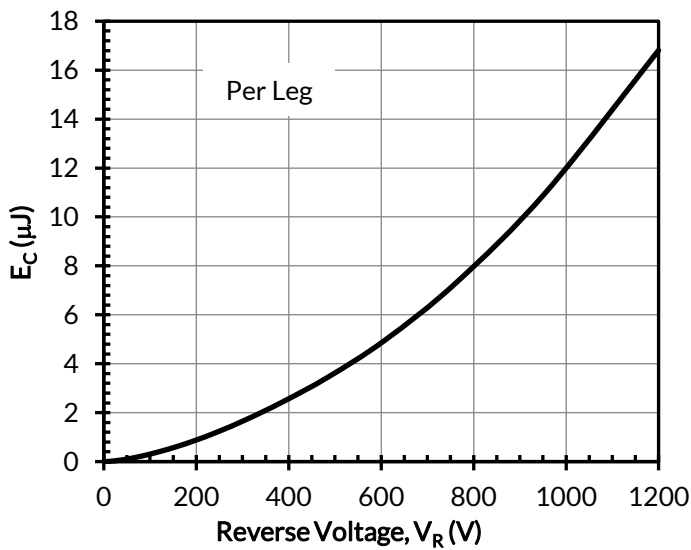


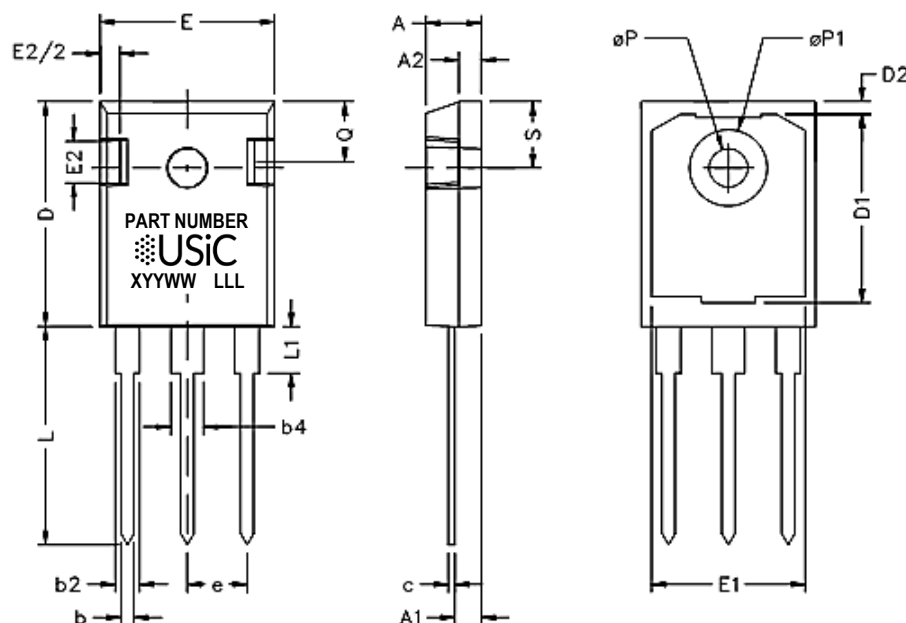
Figure 9. Typical capacitance stored energy vs. reverse voltage

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PACKAGE OUTLINE


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.185	0.209	4.699	5.309
A1	0.087	0.102	2.21	2.61
A2	0.059	0.098	1.499	2.489
b	0.039	0.055	0.991	1.397
b2	0.065	0.094	1.651	2.388
b4	0.102	0.135	2.591	3.429
c	0.015	0.035	0.381	0.889
D	0.819	0.845	20.803	21.463
D1	0.515	-	13.081	-
D2	0.02	0.053	0.508	1.346
E	0.61	0.64	15.494	16.256
e	0.214 BSC		5.44 BSC	
E1	0.53	-	13.462	-
E2	0.135	0.157	3.429	3.988
L	0.78	0.8	19.812	20.32
L1	-	0.177	-	4.496
$\varnothing P$	0.14	0.144	3.556	3.658
$\varnothing P1$	0.278	0.291	7.061	7.391
Q	0.212	0.244	5.385	6.198
S	0.243 BSC		6.17 BSC	

PART MARKING**PART NUMBER**
XYYWW LLL

PART NUMBER = REFER TO
DS_PN DECODER FOR DETAILS

X = ASSEMBLY SITE

YY = YEAR

WW = WORK WEEK

LLL = LOT ID

PACKING TYPE**ANTI-STATIC TUBE****QUANTITY /TUBE : 30 UNITS****DISCLAIMER**

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